



**ELECTRONICS, INC.**  
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## NTE2501 (NPN) & NTE2502 (PNP) Silicon Complementary Transistors High Voltage for Video Output TO-126 Fully Isolated Type Package

**Features:**

- High Breakdown Voltage
- Excellent High Frequency Characteristics

**Applications:**

- High Definition CRT Display
- Color TV Chroma Output, High Breakdown Voltage Drivers

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

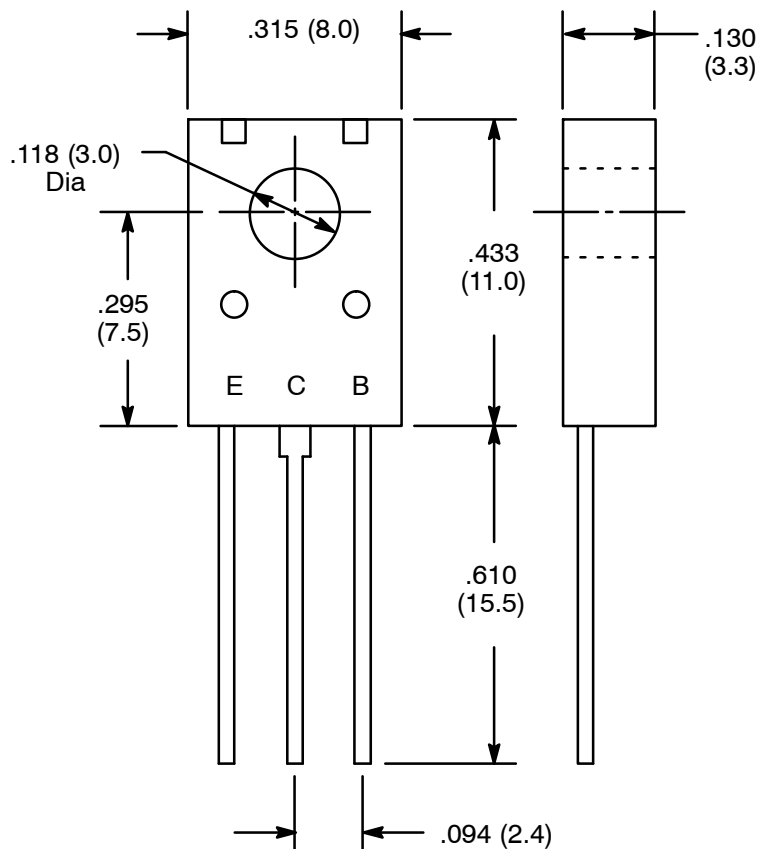
Collector-Base Voltage, $V_{CBO}$ .....	300V
Collector-Emitter Voltage, $V_{CEO}$ .....	300V
Emitter-Base Voltage, $V_{EBO}$ .....	5V
Collector Current, $I_C$	
Continuous .....	100mA
Peak .....	200mA
Collector Dissipation, $P_C$	
$T_A = +25^\circ\text{C}$ .....	1.5W
$T_C = +25^\circ\text{C}$ .....	7W
Operating Junction Temperature, $T_J$ .....	$+150^\circ\text{C}$
Storage Temperature Range, $T_{stg}$ .....	$-55^\circ$ to $+150^\circ\text{C}$

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 200\text{V}, I_E = 0$	-	-	0.1	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4\text{V}, I_C = 0$	-	-	0.1	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 10\text{mA}$	100	-	200	
Gain Bandwidth Product	$f_T$	$V_{CE} = 30\text{V}, I_C = 10\text{mA}$	-	70	-	MHz

**Electrical Characteristics (Cont'd):** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Capacitance NTE2501	$C_{ob}$	$V_{CB} = 30\text{V}, f = 1\text{MHz}$	-	2.6	-	pF
NTE2502			-	3.1	-	pF
Reverse Transfer Capacitance NTE2501	$C_{re}$	$V_{CB} = 30\text{V}, f = 1\text{MHz}$	-	1.8	-	pF
NTE2502			-	2.3	-	pF
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 20\text{mA}, I_B = 2\text{mA}$	-	-	600	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 20\text{mA}, I_B = 2\text{mA}$	-	-	1.0	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	300	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	300	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	5	-	-	V



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